



PTO/SB/08a (03-03)

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Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)			<b>Complete if Known</b>	
			Application Number	10/786,643
			Filing Date	2/25/2004
			First Named Inventor	Cheng, et al.
			Art Unit	2826
			Examiner Name	Quinto, Kevin
			Attorney Docket Number	TSM03-0698
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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
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		Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)				
77	76	EP 0 683 522 A2	11-22-1995	International Business Machines Corporation		
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NON PATENT LITERATURE DOCUMENTS			
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Examiner Signature	Kevin Quinto	Date Considered	2/28/03
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